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Characteristics of Organic Light-Emitting Diodes Using PECCP Langmuir-Blodgett Film as an Emissive Layer

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We have synthesized green light-emitting material, poly(3,6-N-2-ethylhexyl carbazolyl cyanotere-phthalidene)(PECCP), which has an electron-donor and electron-acceptor moiety in a repeated unit of polymer. Organic light-emitting diodes were made with PECCP Langmuir-Blodgett(LB) films in a sandwich structure between indium-tin-oxide(ITO) and aluminum electrodes. Z-type LB films were manufactured using a Kuhn type to use for an emissive layer. We have observed green photoluminescent and electroluminescent spectra at $\lambda_{max}=536$ nm corresponding to 2.31 eV.

Keywords: Organic light-emitting diodes; Langmuir-Blodgett film; PECCP

INTRODUCTION

Organic light-emitting diodes(OLEDs) have received a lot of attention since the first report of efficient visible-light emission from amorphous molecular and polymeric materials[1,2]. The LB technique offers a simple means to deposit high-quality, large-area films of conjugated polymers. Wu et al., fabricated OLEDs using poly(p-phenylene vinylene) (PPV), obtained by thermal treatment of PPV precursor LB films[3]. In this paper, we describe a preparation and characterization of electroluminescent devices using Z-type LB layers of poly(3,6-N-2-ethylhexyl carbazolyl cyanotere-phthalidene) (PECCP).

EXPERIMENTS

Figure 1 shows a molecular structure of PECCP. This material has an electron-donor and an electron-acceptor moiety, and shows a good solubility in common organic solvents such as a chloroform and THF.

R=ethylhexyl group

FIGURE 1. Molecular structure of PECCP.

LB film deposition was undertaken using a Kuhn-type apparatus (NIMA 611). The PECCP was dissolved in chloroform to a concentration of 0.5 g/l. A floating film was prepared by spreading this solution(10 μ l) over the surface of a pure-water subphase at room temperature. Z-type film deposition was performed with a dipping speed of 10 mm/min, and a

transfer ratio of about 1 - 1.2 recorded for each upstroke.

RESULTS AND DISCUSSION

Figure 2a shows a surface pressure(π)-area(A) isotherm of PECCP with barrier compression speed of 50 cm²/min. The PECCP LB films were made at the surface pressure of 20 mN/m. Figure 2b shows a UV/visible absorption and photoluminescence(PL) spectrum of the PECCP LB film. In the UV/visible absorption spectrum, it exhibits a broad absorption band at 410 nm, which may be due to a conjugated double bond. The PECCP LB film shows a PL peak at around $\lambda_{max} = 536$ nm.

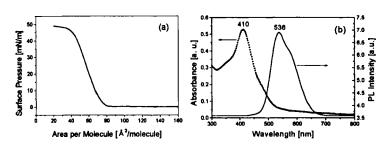


FIGURE 2. (a) π -A isotherm of PECCP molecules, and (b) UV/visible absorption and PL spectrum of the PECCP LB film.

Figure 3a shows a current density-voltage(J-V) characteristics in ITO/PECCP LB film/Al devices. It clearly shows a diode characteristics. Figure 3b shows the EL spectrum in ITO/PECCP LB film/Al structure when the operation voltage is 10 V. It shows that there is a green-light emission with $\lambda_{max} = 536$ nm, which is almost the same as that of PL of the

PECCP LB film. Here, we have used 15 layers of PECCP LB films.

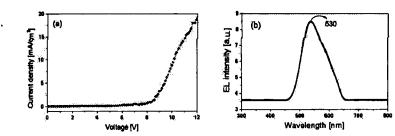


FIGURE 3. (a) Current density-voltage(J-V) characteristics, and (b) EL spectrum in ITO/PECCP LB film/Al device.

CONCLUSION

An electroluminescent diode consisting of LB layers of PECCP sandwiched between ITO and aluminum electrodes has been fabricated. Above a threshold bias voltage of ca. 6 V, green light emission was observed, which has $\lambda_{max}=536$ nm. We are going to study on recombination zone in OLEDs using the LB films by varying the film thickness.

Acknowledgment

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